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Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: October 31, 2000

Group: 2823

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
AKS	5,403,772	04/04/95	Zhang et al			
AKS	5,426,064	06/20/95	Zhang et al			
AKCS	5,481,121	01/02/96	Zhang et al			
AKCS	5,488,000	01/30/96	Zhang et al			
AKCS	5,492,843	02/20/96	Adachi et al			
AKCS	5,501,989	03/26/96	Takayama et al			
AKCS	5,508,533	04/16/96	Takemura			
AKCS	5,529,937	06/25/96	Zhang et al			
AKCS	5,534,716	07/09/96	Takemura			
AKCS	5,543,352	08/06/96	Ohtani et al			
AKCS	5,563,426	10/08/96	Zhang et al			
AKCS	5,569,610	10/29/96	Zhang et al			
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AKCS	5,580,792	12/03/96	Zhang et al			
AKCS	5,585,291	12/17/96	Ohtani et al			
AKCS	5,589,694	12/31/96	Takayama et al			
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AKCS	5,639,698	06/17/97	Yamazaki			
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AKS	5,504,019	04/02/96	Miyasaka et al.			
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Examiner

Asok Kumar Sardar

Date Considered

4/3/01

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
AKS	5,595,923	01/21/97	Zhang et al			
AKS	5,595,944	01/21/97	Zhang et al			
AKS	5,604,360	02/18/97	Zhang et al			
AKS	5,605,846	02/25/97	Ohtani et al			
AKS	5,606,179	02/25/97	Yamazaki et al			
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AKS	5,612,250	03/18/97	Ohtani et al			
AKS	5,614,426	03/25/97	Funada et al			
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AKS	5,616,506	04/01/97	Takemura			
AKS	5,620,910	04/15/97	Teramoto			
AKS	5,621,224	04/15/97	Yamazaki et al			
AKS	5,624,851	04/29/97	Takayama et al			
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AKS	5,643,826	07/01/97	Ohtani et al			
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AKS	Wolf et al., "Silicon Processing for the VLSI Era", Vol. 1, pgs 550-551, 1986.

Examiner Asok Kumar Sarkar Date Considered 4/3/01

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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Shunpei YAMAZAKI et al. <i>09/699,466</i>	
		Filing Date: October 31, 2000	Group: 2823

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AICS	5,744,822	04/28/98	Takayama et al.	257	66	
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AICS	5,766,977	06/16/98	Yamazaki	438	151	
AUS	5,773,846	06/30/98	Zhang et al.	257	66	
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Examiner Asok Kumar Sutkar Date Considered 4/3/01

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AKS	61-63107	04/01/86	Japan			Abstract	
AKS	3-280420 (Japanese & English)	12/11/91	Japan			Full	
AKS	5-82442	04/02/93	Japan			Abstract	
AKS	7-16134	06/23/95	Japan			Abstract	
AKS	2-140915	05/20/90	Japan			Full	
AKS	1-206632	08/18/89	Japan			Abstract	
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AKS	0178447	09/10/84	European			Full	
AKS	6-0105216	10/06/85	Japan			Full	
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